

Application Manual

MCSO2E

**High Temperature
Clock Oscillator
15 kHz – 100 MHz**

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MCSO2E

High Temperature Clock Oscillator 15 kHz – 100 MHz

1. OVERVIEW

- Oscillator with built-in AT-cut crystal, operating in fundamental mode
- Overall frequency stability over temperature range:
 - $\leq \pm 100$ ppm at C = -55 to +125°C
 - $\leq \pm 150$ ppm at E = -55 to +150°C
 - $\leq \pm 300$ ppm at D = -55 to +175°C
 - $\leq \pm 400$ ppm at G = -55 to +210°C
- Frequency stability guaranteed for 1000 h at T_{MAX}
- Very fast start-up: typ.1 ms at 25°C
- Output signal HCMOS compatible
- High shock and vibration resistance
- Operating voltage: 2.5 V, 3.3 V or 5.0 V
- Power consumption:
 - $< 110 \mu\text{A}$ at $V_{DD} = 3.3 \text{ V}$, $F = 32.768 \text{ kHz}$, low power type (L)
 - $< 5 \text{ mA}$ at $V_{DD} = 3.3 \text{ V}$, $F \leq 20 \text{ MHz}$
- Operating temperature range:
 - C = -55 to +125°C
 - E = -55 to +150°C
 - D = -55 to +175°C
 - G = -55 to +210°C
 - X = Custom
- Enable/Disable function (option 1)
 - Standby current $I_{DD} < 10 \mu\text{A}$ for low power type (L)
- Low aging rate
- Ceramic SMD package (5.0 x 3.2 mm), RoHS-compliant and 100% lead-free

1.1. GENERAL DESCRIPTION

The MCSO2E combines a High Temperature, High Frequency HCMOS oscillator circuitry together with an AT-cut quartz crystal in a hermetically sealed ceramic package with ceramic lid (G version with metal lid). No external components are required.

The frequency output 15 kHz – 100 MHz on F_{OUT} pin can be enabled / disabled by the E/D pin (option 1). The F_{OUT} frequency is enabled when E/D pin is connected to V_{DD} or when it is left open (not connected). When the E/D pin is tied to GND the frequency is disabled and the F_{OUT} pin is in high impedance state (Hi-Z).

1.2. APPLICATIONS

The MCSO2E clock oscillator module combines outstanding performance and robustness in a standard ceramic package:

- Oscillator module (embedded XTAL) in a standard 5.0 x 3.2 mm lead-free ceramic package
- Temperature range up to +210°C
- High shock and vibration resistant

The robust construction and high performances make this product perfectly suitable for many high reliability applications:

- Harsh Environment: Geothermal Equipment, Down Hole and Well Drilling
- Avionics / Aerospace: Airborne Equipment / Engine Control / Actuator Controller / Temperature Controller / Instrumentation / Navigation and Guidance Systems
- Instrumentation: Field Test Instrument / Automotive Test Equipment
- Security / Safety: Survival and Protection System / Railway Security System / Fire Fighter Equipment
- Industrial: Telemetry / A/C Controller / Hydraulic Sensor

1.3. ORDERING INFORMATION

Example: MCSO2E _ H V – D 24.000 MHz E/D T3 XXX

Code	Package Size
MCSO2E	5.0 x 3.2 mm

Code	Power consumption
L (32.768 kHz)	Low power
Blank	Standard

Code	Frequency range
H	> 20 MHz
Blank	≤ 20 MHz

Code	Supply voltage
W	$V_{DD} = 2.5\text{ V}$
V	$V_{DD} = 3.3\text{ V}$
Blank	$V_{DD} = 5.0\text{ V}$

Code	Temperature range
C	-55 to +125°C
E	-55 to +150°C
D	-55 to +175°C
G	-55 to +210°C *
X	Custom

Code	Frequency
24.000 MHz	24.000 MHz

Code	Option 1
E/D	Enable/Disable
Blank	No function

Code	Option 2
T3	SnAgCu solder dipped pads **
Blank	Au flashed pads

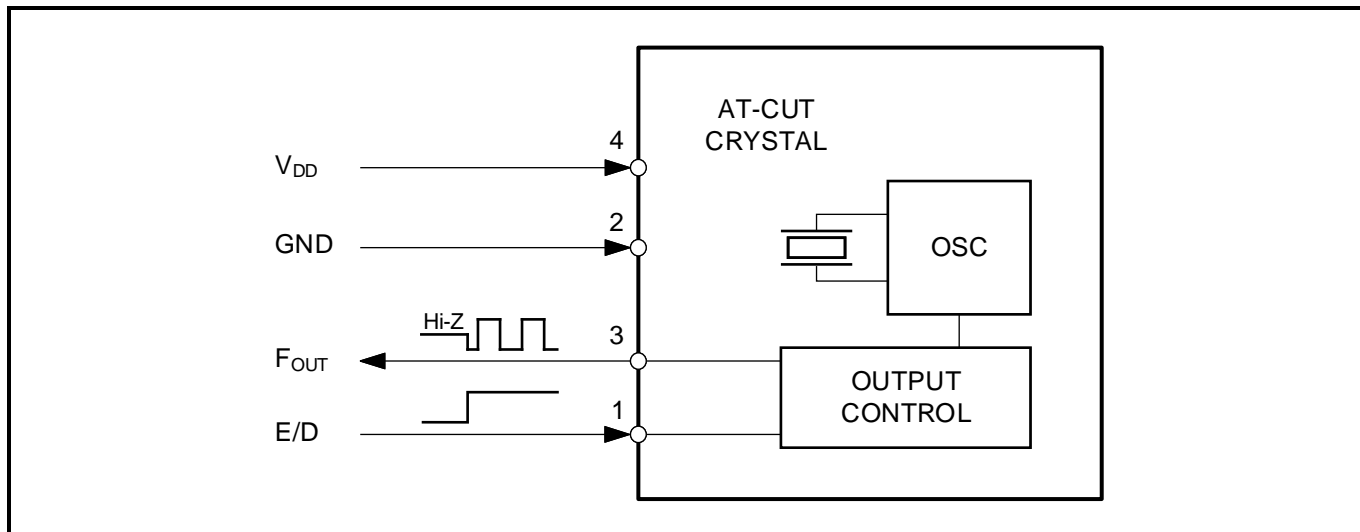
Code	Customer specification N°
XXX	XXX

* For the low consumption version (L), G version is only available as 5.0 V version and the G range is limited to +200°C.

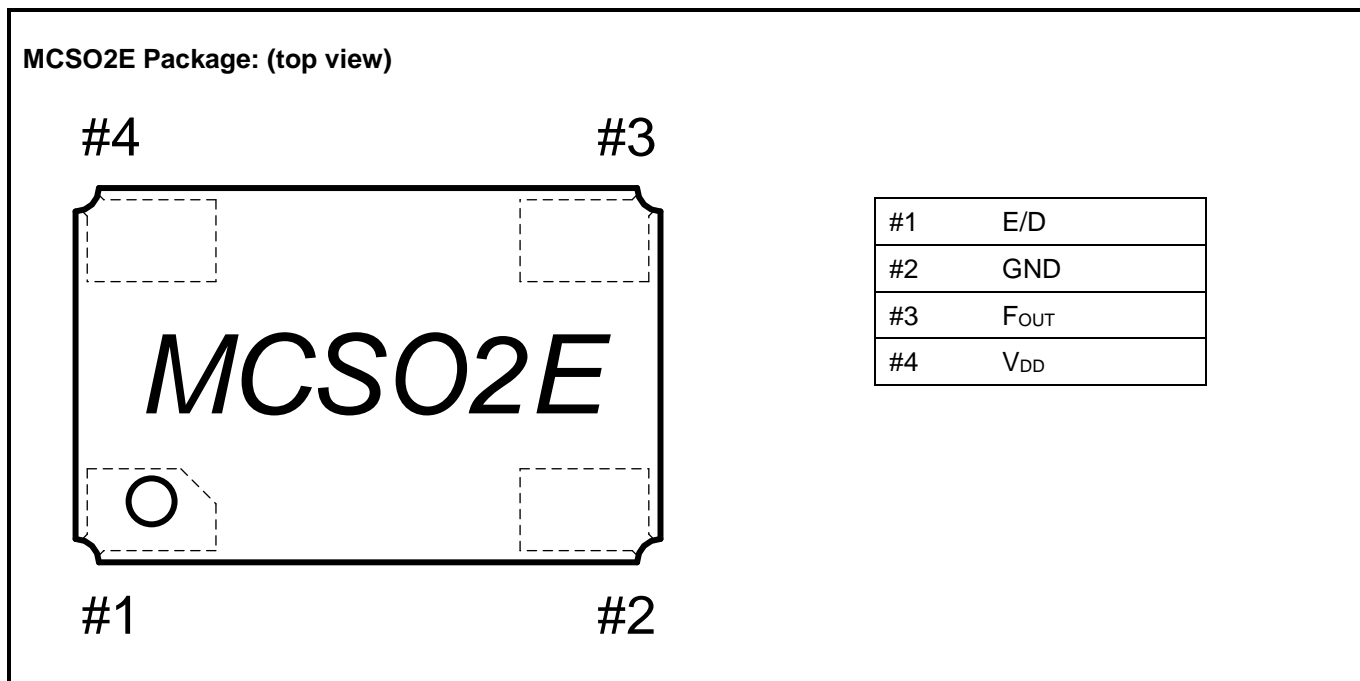
Kovar lid on G range version.

** T3 not available for G range version.

2. BLOCK DIAGRAM



2.1. PINOUT



2.2. PIN DESCRIPTION

Symbol	Pin #	Description
E/D	1	Input to enable/disable the F _{OUT} pin (option 1). If E/D is HIGH or floating (V _{IH} or open), the F _{OUT} pin is in output mode. When E/D is tied to Ground (V _{IL}), the F _{OUT} pin is disabled (Hi-Z).
GND	2	Ground.
F _{OUT}	3	Clock Output; three-state; controlled by E/D. If E/D is HIGH (V _{DD}) or floating, the F _{OUT} pin drives the square wave of the frequency. When E/D is tied to Ground, the F _{OUT} pin is disabled (Hi-Z).
V _{DD}	4	Power Supply Voltage.

3. ELECTRICAL SPECIFICATIONS

3.1. ABSOLUTE MAXIMUM RATINGS

Absolute Maximum Ratings according to IEC 60134:

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{DD}	Power supply voltage	Nominal V _{DD} = 2.5 V	-0.3	3	V
		Nominal V _{DD} = 3.3 V	-0.3	3.8	
		Nominal V _{DD} = 5.0 V	-0.3	5.5	
V _I	Input voltage		-0.3	V _{DD}	V
V _O	Output voltage		-0.3	V _{DD}	V
V _{ESD}	ESD voltage	HBM (1)		±2000	V
		MM (2)		±200	
T _C	Operating temperature range C		-55	125	°C
T _E	Operating temperature range E		-55	150	°C
T _D	Operating temperature range D		-55	175	°C
T _G	Operating temperature range G		-55	210	°C
T _{STO}	Storage temperature	Stored as bare product	-65	125	°C
T _{PEAK}	Maximum reflow condition	JEDEC J-STD-020C		265	°C

(1) HBM: Human Body Model, according to JESD22-A114.

(2) MM: Machine Model, according to JESD22-A115.

3.2. OPERATING PARAMETERS

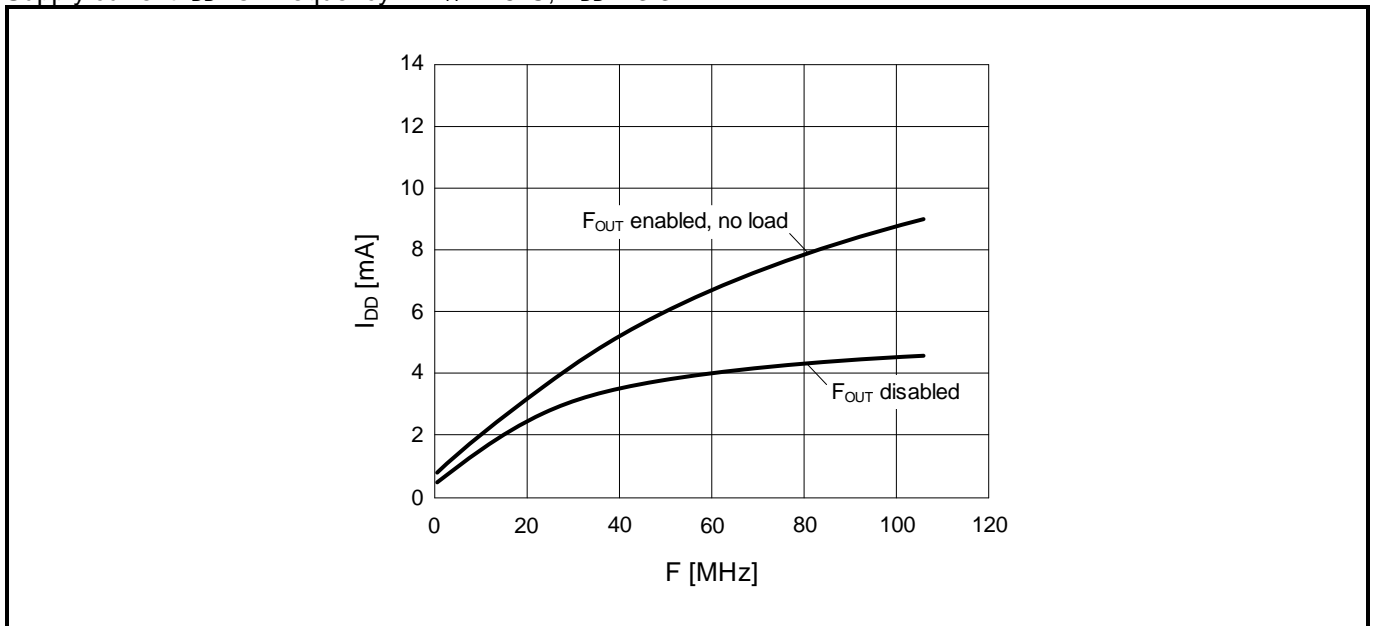
For this Table, V_{DD} = nominal voltage; GND = 0 V; T_A = 25 °C; unless otherwise indicated.

Operating Parameters:

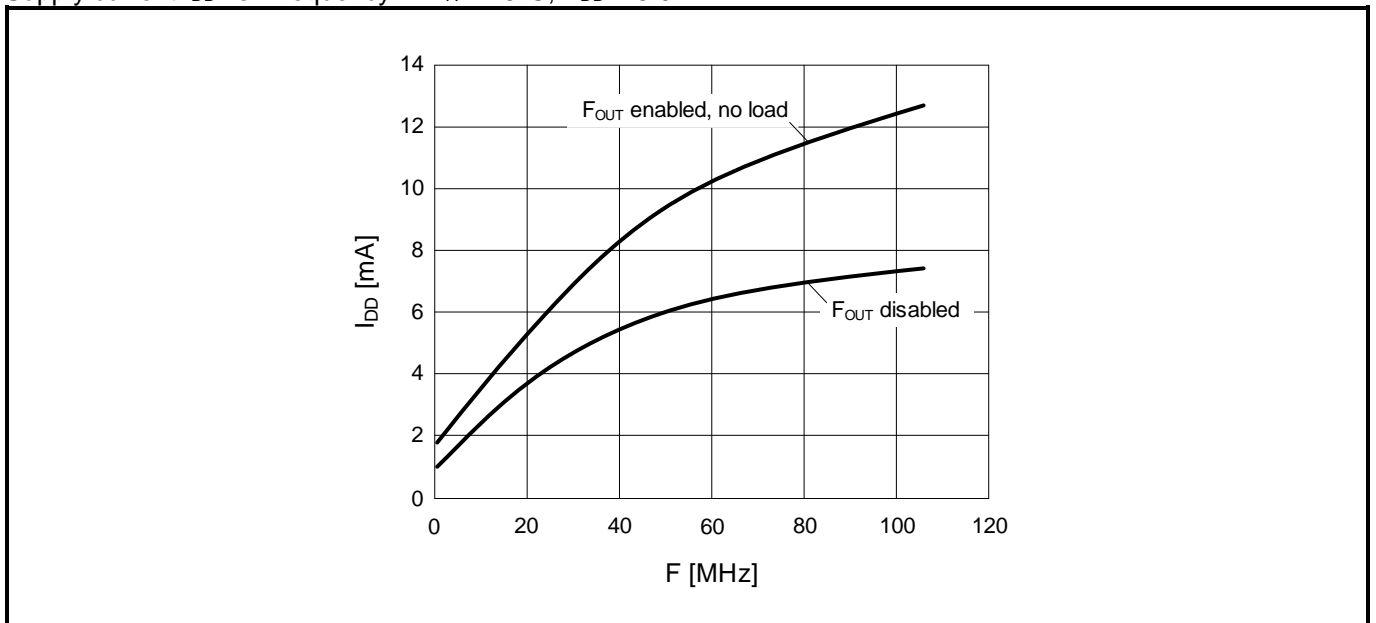
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Supply						
V_{DD}	Power supply voltage (1)	Nominal $V_{DD} = 2.5$ V	2.375		2.625	V
		Nominal $V_{DD} = 3.3$ V	3.135		3.465	
		Nominal $V_{DD} = 5.0$ V	4.75		5.25	
I_{DD}	Input current. $V_{DD} = 2.5$ V F_{OUT} enabled, no load (For L version, $C_L = 10$ pF)	15 kHz $\leq F \leq 32.768$ kHz (L)			0.1	mA
		32.768 kHz $< F \leq 10$ MHz			2	
		10 MHz $< F \leq 20$ MHz			3	
		20 MHz $< F \leq 100$ MHz			15	
	Input current. $V_{DD} = 3.3$ V F_{OUT} enabled, no load (For L version, $C_L = 10$ pF)	15 kHz $\leq F \leq 32.768$ kHz (L)			0.11	
		32.768 kHz $< F \leq 10$ MHz			4	
		10 MHz $< F \leq 20$ MHz			5	
		20 MHz $< F \leq 100$ MHz			20	
	Input current. $V_{DD} = 5.0$ V F_{OUT} enabled, no load (For L version, $C_L = 10$ pF)	15 kHz $\leq F \leq 32.768$ kHz (L)			0.12	
		32.768 kHz $< F \leq 10$ MHz			6	
		10 MHz $< F \leq 20$ MHz			7	
		20 MHz $< F \leq 100$ MHz			30	
I_{DDD}	Standby current. Input current. Output disabled	L version (For standard version, see TYPICAL CHARACTERISTICS)			10	μ A
Input E/D						
V_I	Input voltage		GND -0.3		$V_{DD} +0.3$	V
V_{IL}	LOW level input voltage		GND		$0.3 V_{DD}$	V
V_{IH}	HIGH level input voltage		$0.7 V_{DD}$		V_{DD}	V
t	Reaction time	Standard version			1	μ s
		L version			5	ms
Output F_{OUT} (HCMOS compatible)						
V_{OH}	HIGH level output voltage		$V_{DD} -0.5$			V
V_{OL}	LOW level output voltage				0.4	V
C_L	Output load capacitance, HCMOS	Standard version	3	15	47	pF
		L version			27	
t_r / t_f	Rise & fall time	L version $C_L = 15$ pF, 20% to 80% V_{DD}			25	ns
		$F \leq 20$ MHz, $C_L = 15$ pF, 20% to 80% V_{DD}			7	
		$F > 20$ MHz, $C_L = 15$ pF, 10% to 90% V_{DD}			3	
(1) A 47 nF decoupling capacitor has to be connected between V_{DD} and GND.						

3.3. TYPICAL CHARACTERISTICS

Supply current I_{DD} vs. Frequency F: $T_A = 25^\circ\text{C}$, $V_{DD} = 3.3\text{ V}$



Supply current I_{DD} vs. Frequency F: $T_A = 25^\circ\text{C}$, $V_{DD} = 5.0\text{ V}$



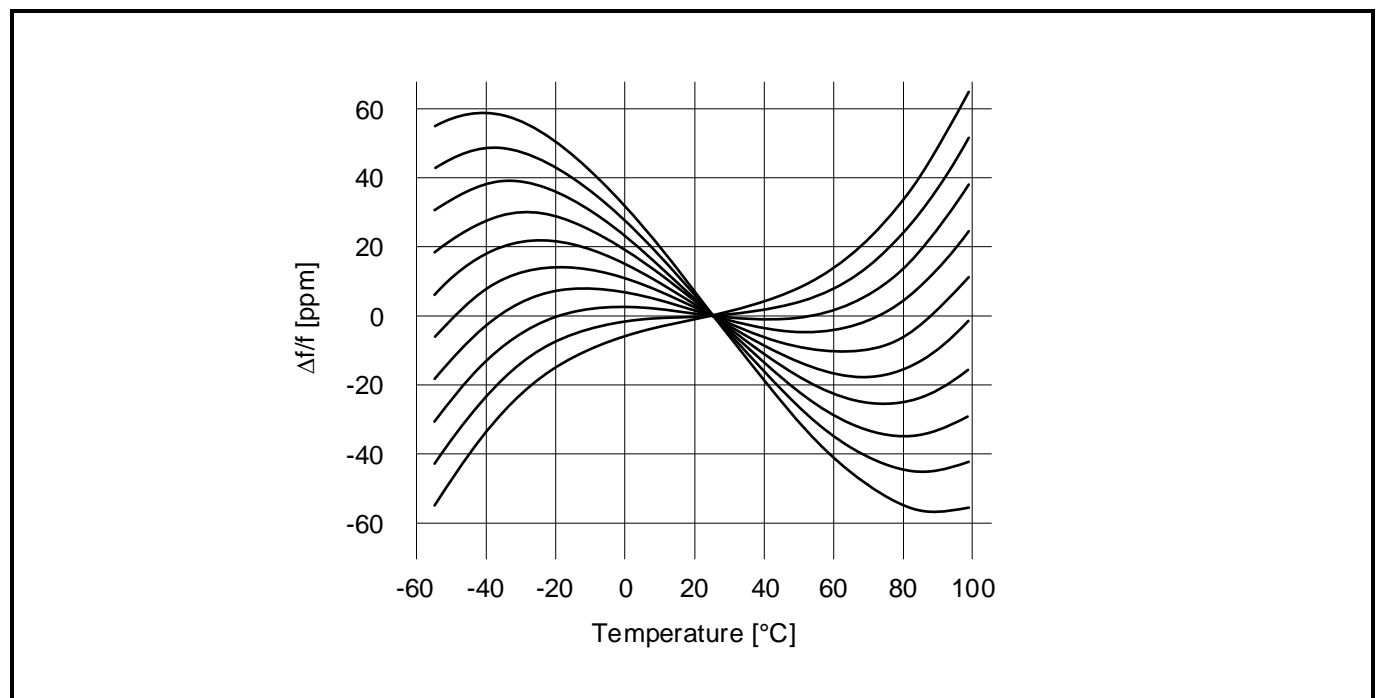
3.4. OSCILLATOR PARAMETERS

For this Table, V_{DD} = nominal voltage; GND = 0 V; T_A = 25 °C; unless otherwise indicated.

Oscillator Parameters:

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
General						
F	Frequency range		0.015		100	MHz
t_{START}	Oscillator start-up time			1	5	ms
δ_{FOUT}	F_{OUT} duty cycle @ $V_{DD}/2$		40		60	%
Frequency Characteristics						
$\Delta F/F$	Overall frequency stability over temperature range (see ORDERING INFORMATION)	Including adjustment at +25°C, long term aging 1000 h at T_{MAX} , V_{DD} variations $\pm 5\%$ and C_L variations min. to max. C = -55 to +125°C E = -55 to +150°C D = -55 to +175°C G = -55 to +210°C (1)			± 100 ± 150 ± 300 ± 400	ppm
(1) For the low consumption version (L), G version is only available as 5.0 V version and the G range is limited to +200°C.						

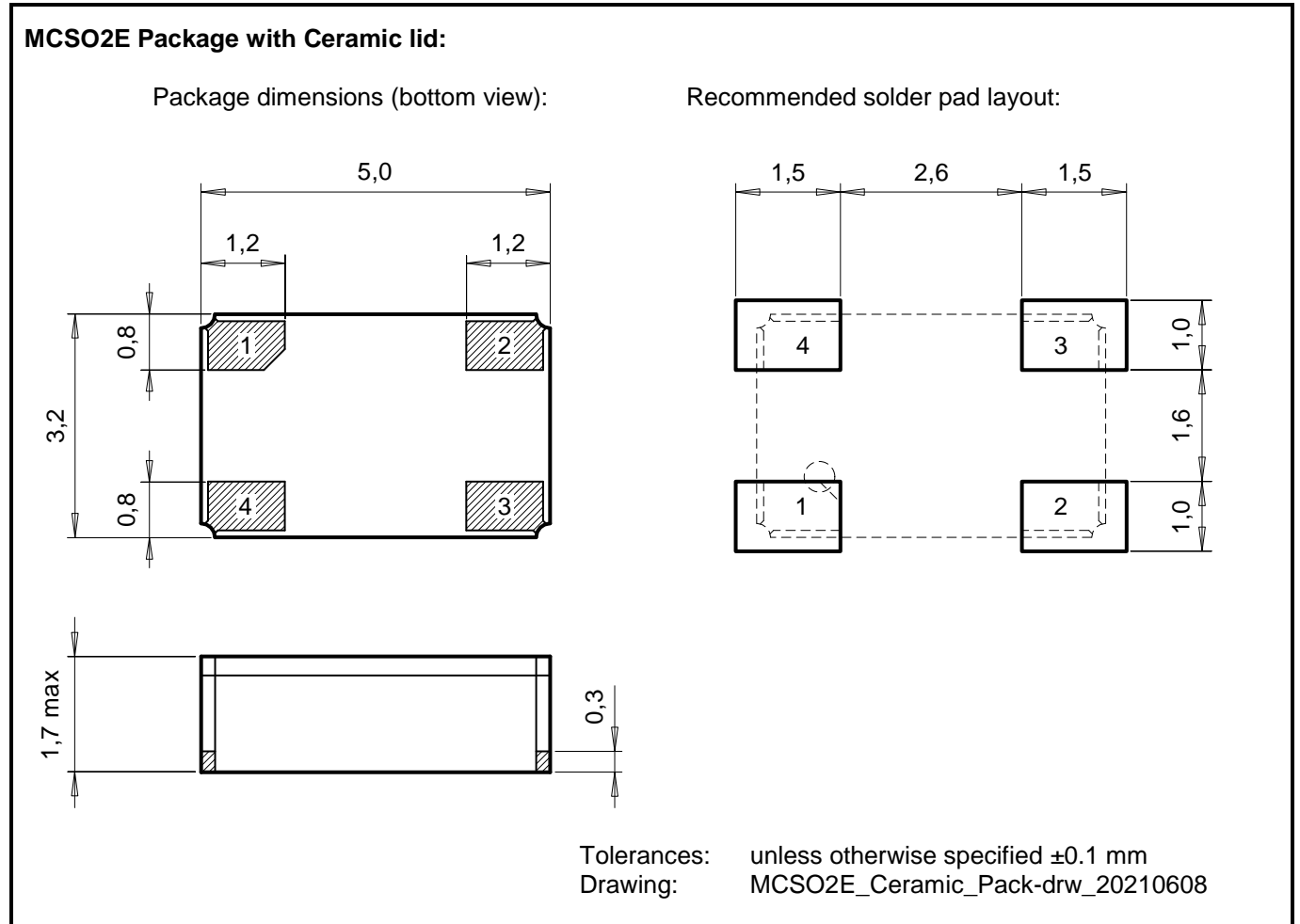
3.4.1.FREQUENCY VS. TEMPERATURE CHARACTERISTICS



4. PACKAGE

4.1. DIMENSIONS AND SOLDER PAD LAYOUT

4.1.1. PACKAGE WITH CERAMIC LID

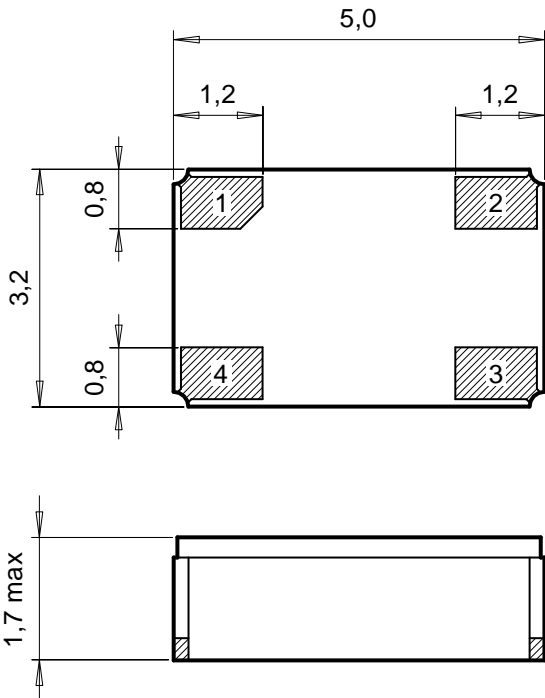


All dimensions in mm typical.

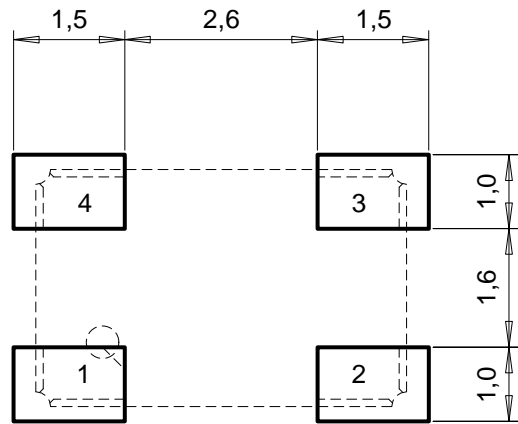
4.1.2. PACKAGE WITH METAL LID (FOR G RANGE VERSION)

MCSO2E Package with Metal lid (for G range version):

Package dimensions (bottom view):



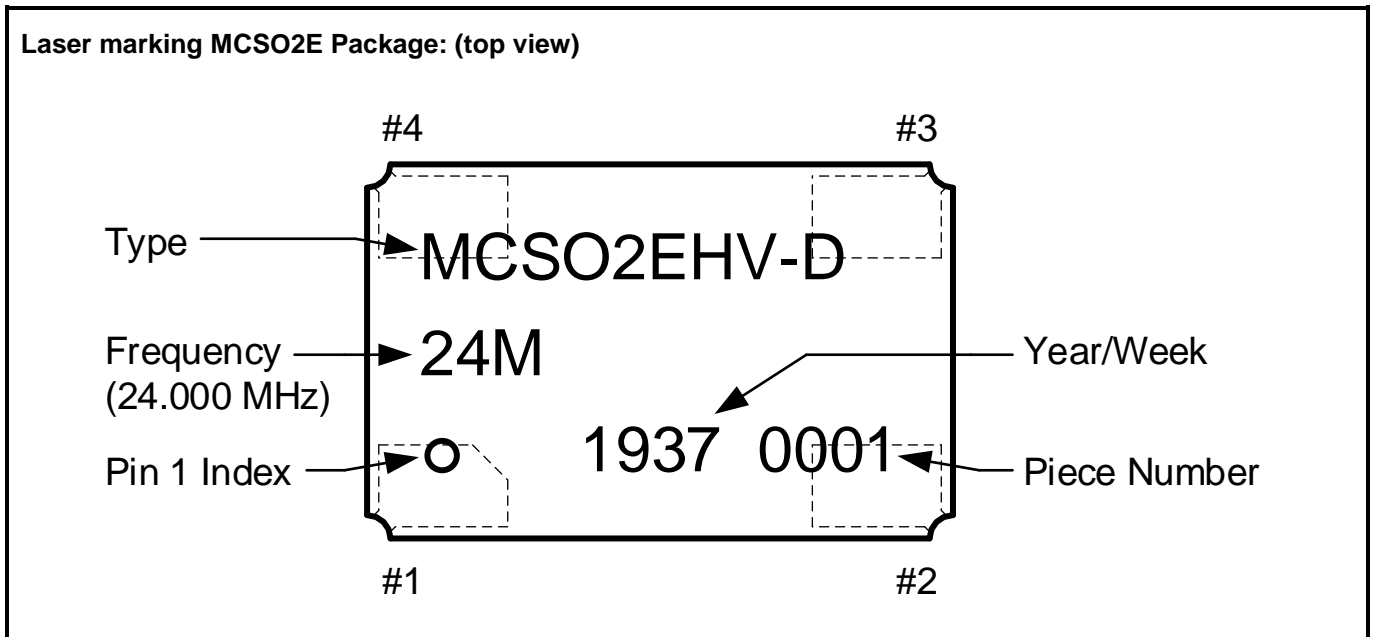
Recommended solder pad layout:



Tolerances: unless otherwise specified ± 0.1 mm
Drawing: MCSO2E_Metal_Pack-drw_20210608

All dimensions in mm typical.

4.2. MARKING AND PIN #1 INDEX

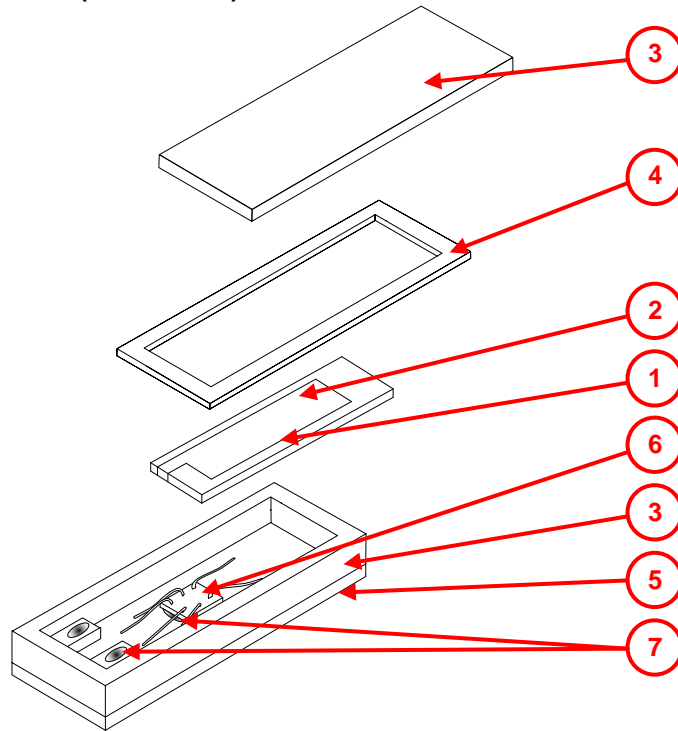


5. MATERIAL COMPOSITION DECLARATION & ENVIRONMENTAL INFORMATION

5.1. HOMOGENOUS MATERIAL COMPOSITION DECLARATION (CERAMIC LID)

Homogenous material information according to IPC-1752 standard

Material Composition MCSO2E (Ceramic lid):



(Symbolic drawing)



No.	Item Component Name	Sub Item Material Name	Material Weight		Substance Element	CAS Number	Comment
			(mg)	(%)			
1	Resonator	Quartz Crystal	3.7	100%	SiO ₂	14808-60-7	
2	Electrodes	Cr+Au	0.2	5%	Cr	Cr: 7440-47-3	
				95%	Au	Au: 7440-57-5	
3	Housing	Ceramic	63.1	100%	Al ₂ O ₃	1344-28-1	
4	Seal	Solder Preform	3.6	80%	Au80 / Sn20	Au: 7440-57-5	
				20%		Sn: 7440-31-5	
5	Terminations	Internal and external terminals	5.1	80%	W	W: 7440-33-7	Tungsten
				15%	Ni	Ni: 7440-02-0	Nickel plating
				5%	Au 0.3 micron	Au: 7440-57-5	Gold plating
6	HCMOS IC	Silicon	1.0	95%	Si	Si: 7440-21-3	
		Die pad plating		1%	Al	Al: 7429-90-5	
		Bonding wires		4%	Al	Al: 7429-90-5	
7	Conductive adhesive	Silver filled Epoxy	1.3	70%	Ag	Ag: 7440-22-4	
				30%	EP	129915-35-1	
		Unit weight typ. ±10%	78				

5.2. RECYCLING MATERIAL INFORMATION (CERAMIC LID)

Recycling material information according to IPC-1752 standard.

Element weight is accumulated and referenced to the unit weight of 78 mg.

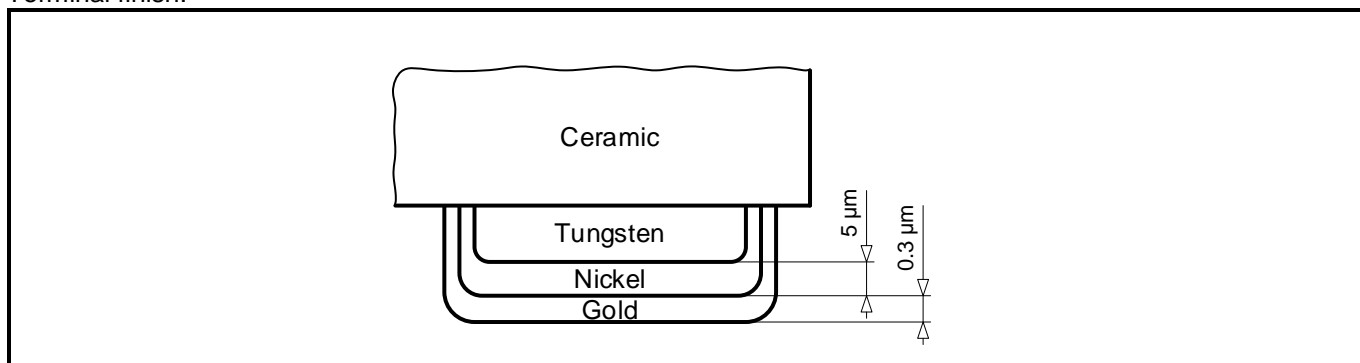
Item Material Name	No.	Item Component Name	Material Weight		Substance Element	CAS Number	Comment
			(mg)	(%)			
Quartz Crystal	1	Resonator	3.7	4.74	SiO ₂	14808-60-7	
Chromium	2	Electrodes	0.01	0.013	Cr	Cr: 7440-47-3	
Ceramic	3	Housing	63.1	80.9	Al ₂ O ₃	1344-28-1	
Gold	2	Electrodes	3.32	4.26	Au	Au: 7440-57-5	
	4	Seal					
	5	Terminations					
Tin	4	Seal	0.72	0.92	Sn	Sn: 7440-31-5	
Nickel	5	Terminations	0.77	0.98	Ni	Ni: 7440-02-0	
Tungsten	5	Terminations	4.08	5.23	W	W: 7440-33-7	
Silicon	6a	HCMOS IC	0.95	1.22	Si	Si: 7440-21-3	
Aluminum	6b	HCMOS IC	0.05	0.06	Al	Al: 7429-90-5	
	6c	HCMOS IC					
Silver	7a	Conductive adhesive	0.91	1.17	Ag	Ag: 7440-22-4	
Epoxy	7b	Conductive adhesive	0.39	0.50	EP	129915-35-1	
Unit weight (total) typ. ±10%			78	100			

5.3. ENVIRONMENTAL PROPERTIES & ABSOLUTE MAXIMUM RATINGS (CERAMIC LID)

Package	Description
DFN-4 ceramic package	Dual Flat No Leads (DFN), hermetically sealed ceramic package with ceramic lid.

Parameter	Directive	Conditions	Value
Product weight (total)			78 mg
Storage temperature		Store as bare product	-65 to +125°C
Moisture sensitivity level (MSL)	IPC/JEDEC J-STD-020D		MSL1
MTTF			> 100 years

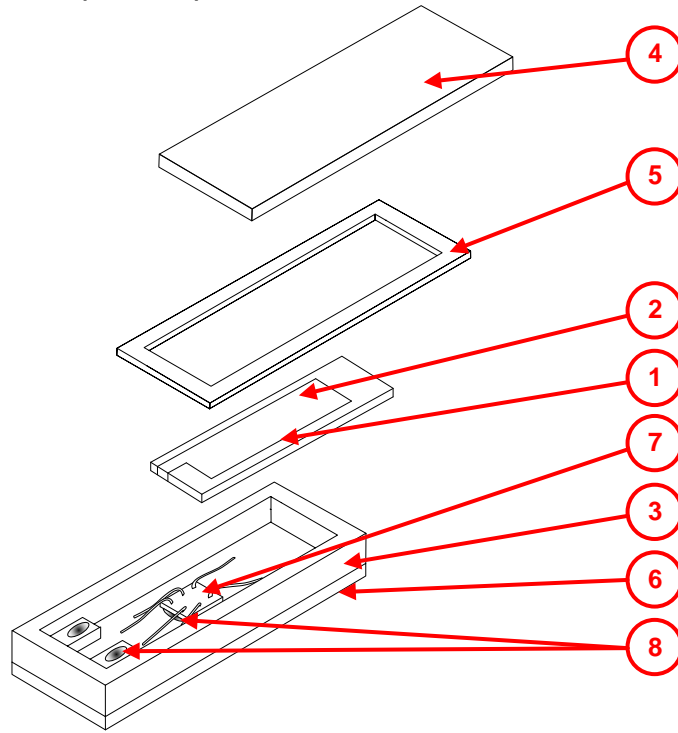
Terminal finish:



5.4. HOMOGENOUS MATERIAL COMPOSITION DECLARATION (METAL LID)

Homogenous material information according to IPC-1752 standard

Material Composition MCSO2E (Metal lid):



(Symbolic drawing)



No.	Item Component Name	Sub Item Material Name	Material Weight		Substance Element	CAS Number	Comment
			(mg)	(%)			
1	Resonator	Quartz Crystal	3.7	100%	SiO ₂	14808-60-7	
2	Electrodes	Cr+Au	0.2	5%	Cr	Cr: 7440-47-3	
				95%	Au	Au: 7440-57-5	
3	Housing	Ceramic	48.7	100%	Al ₂ O ₃	1344-28-1	
4	Metal Lid	Kovar Lid	32.0	90%	Fe53Ni29Co18	Fe: 7439-89-6 Ni: 7440-02-0 Co: 7440-48-4	
				9%	Ni	Ni: 7440-02-0	Nickel plating
				1%	Au	Au: 7440-57-5	Gold plating
5	Seal	Solder Preform	3.6	80% 20%	Au80 / Sn20	Au: 7440-57-5 Sn: 7440-31-5	
6	Terminations	Internal and external terminals	3.5	80%	W	W: 7440-33-7	Tungsten
				15%	Ni	Ni: 7440-02-0	Nickel plating
				5%	Au 0.3 micron	Au: 7440-57-5	Gold plating
7	HCMOS IC	Silicon Die pad plating Bonding wires	1.0	95%	Si	Si: 7440-21-3	
				1%	Al	Al: 7429-90-5	
				4%	Al	Al: 7429-90-5	
8	Conductive adhesive	Silver filled Epoxy	1.3	70%	Ag	Ag: 7440-22-4	
				30%	EP	129915-35-1	
		Unit weight typ. ±10%	94				

5.5. RECYCLING MATERIAL INFORMATION (METAL LID)

Recycling material information according to IPC-1752 standard.

Element weight is accumulated and referenced to the unit weight of 94 mg.

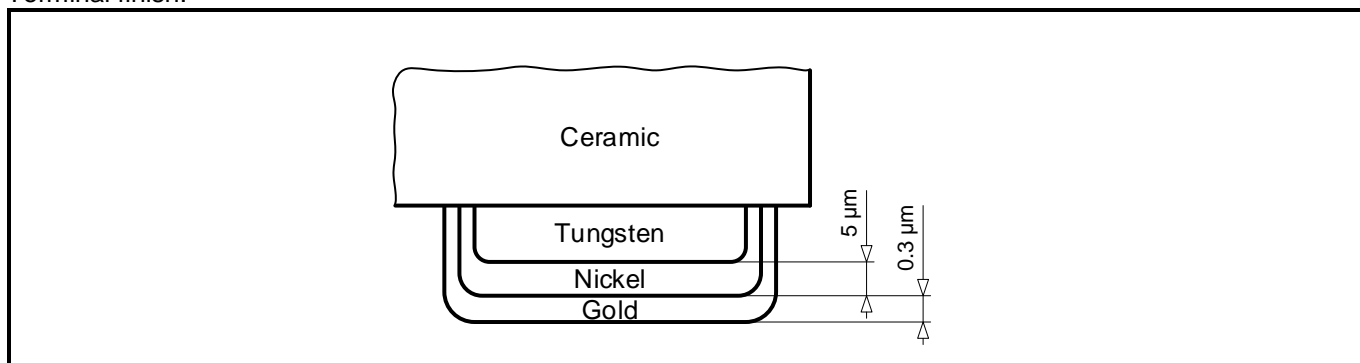
Item Material Name	No.	Item Component Name	Material Weight		Substance Element	CAS Number	Comment
			(mg)	(%)			
Quartz Crystal	1	Resonator	3.7	3.94	SiO ₂	14808-60-7	
Chromium	2	Electrodes	0.01	0.011	Cr	Cr: 7440-47-3	
Ceramic	3	Housing	48.7	51.8	Al ₂ O ₃	1344-28-1	
Gold	2	Electrodes	3.56	3.79	Au	Au: 7440-57-5	
	4	Metal Lid					
	5	Seal					
	6	Terminations					
Tin	5	Seal	0.72	0.77	Sn	Sn: 7440-31-5	
Nickel	4	Metal Lid (Plating)	3.41	3.62	Ni	Ni: 7440-02-0	
	6	Terminations					
Tungsten	6	Terminations	2.80	2.98	W	W: 7440-33-7	
Kovar	4	Metal Lid	28.8	30.6	Fe53Ni29Co18	Fe: 7439-89-6	
						Ni: 7440-02-0	
						Co: 7440-48-4	
Silicon	7a	HCMOS IC	0.95	1.01	Si	Si: 7440-21-3	
Aluminum	7b	HCMOS IC	0.05	0.05	Al	Al: 7429-90-5	
	7c	HCMOS IC					
Silver	8a	Conductive adhesive	0.91	0.97	Ag	Ag: 7440-22-4	
Epoxy	8b	Conductive adhesive	0.39	0.41	EP	129915-35-1	
Unit weight (total) typ. ±10%			94	100			

5.6. ENVIRONMENTAL PROPERTIES & ABSOLUTE MAXIMUM RATINGS (METAL LID)

Package	Description
DFN-4 ceramic package	Dual Flat No Leads (DFN), hermetically sealed ceramic package with metal lid.

Parameter	Directive	Conditions	Value
Product weight (total)			94 mg
Storage temperature		Store as bare product	-65 to +125°C
Moisture sensitivity level (MSL)	IPC/JEDEC J-STD-020D		MSL1
MTTF			> 100 years

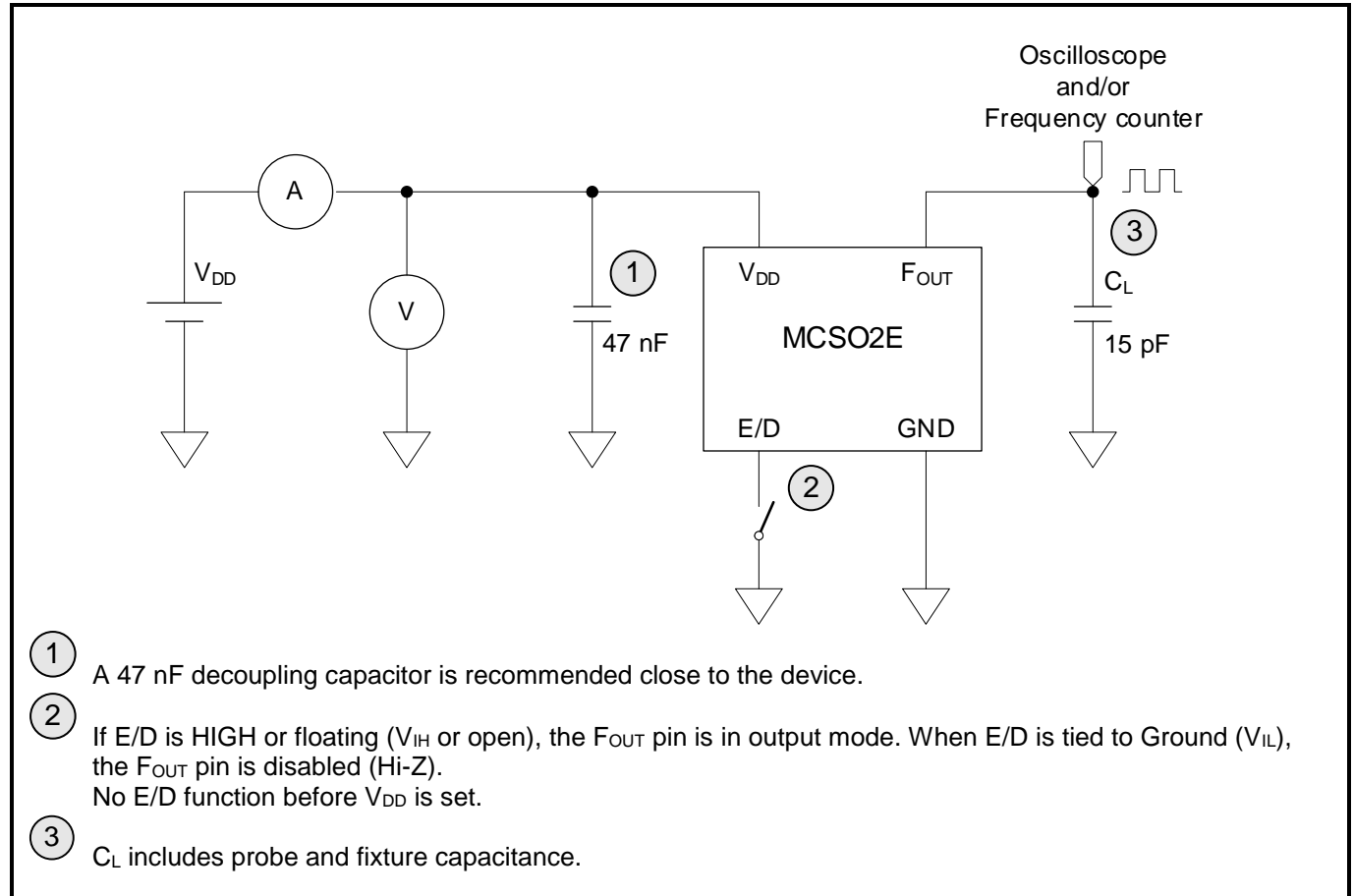
Terminal finish:



6. APPLICATION INFORMATION

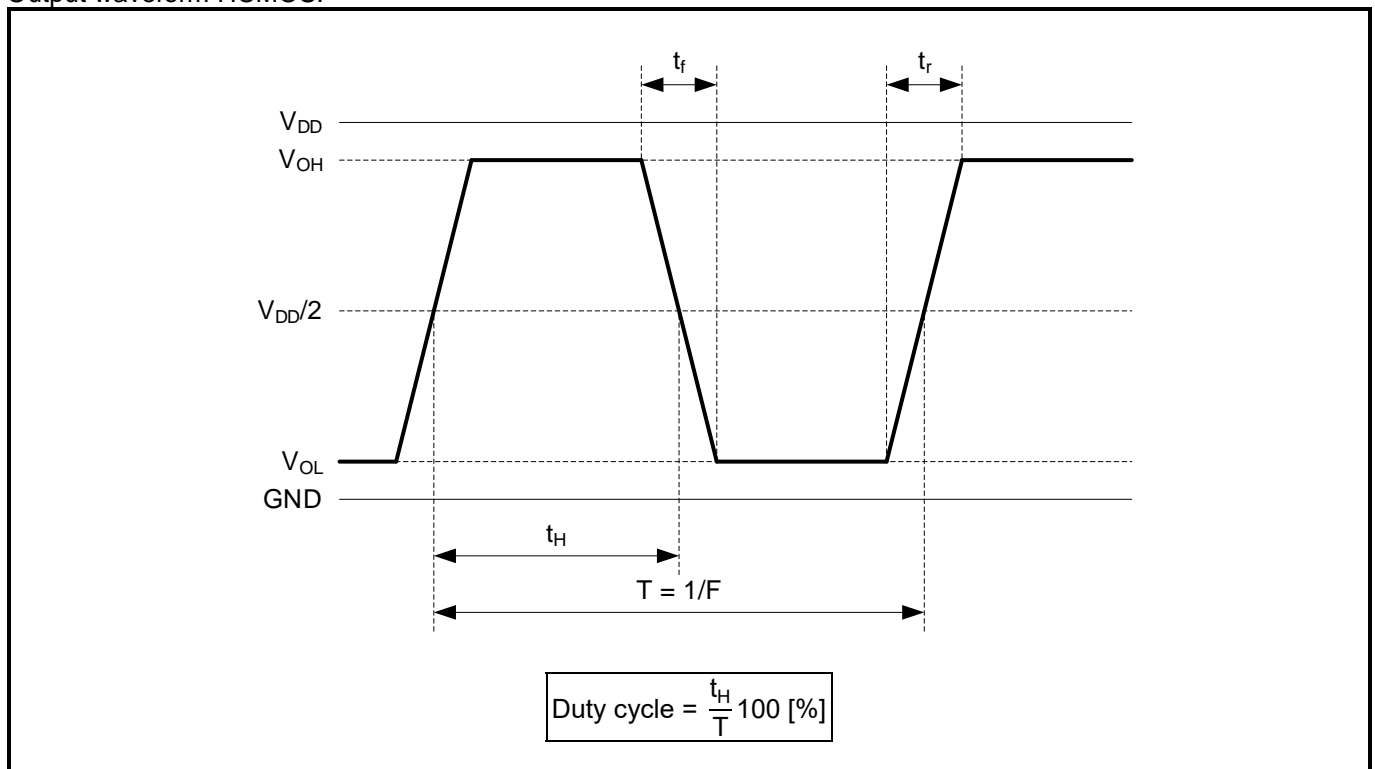
6.1. TEST CIRCUIT

Test circuit HCMOS:



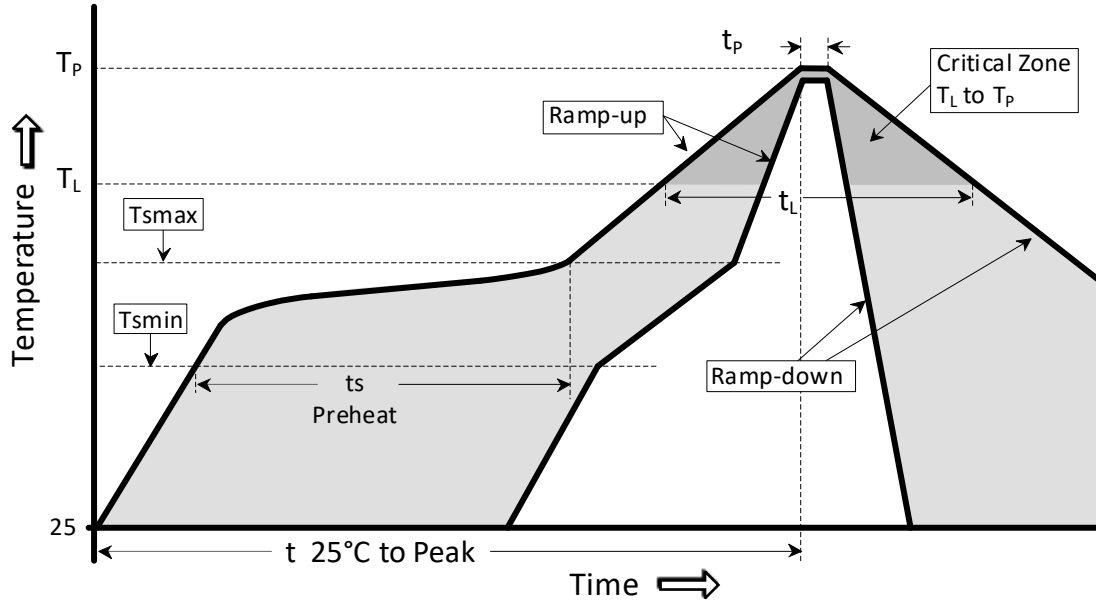
6.2. OUTPUT WAVEFORM

Output waveform HCMOS:



6.3. SOLDERING INFORMATION

Maximum Reflow Conditions in accordance with IPC/JEDEC J-STD-020C “Pb-free”



Temperature Profile	Symbol	Condition	Unit
Average ramp-up rate	(T_{Smax} to T_P)	3°C / second max	°C / s
Ramp down Rate	T_{cool}	6°C / second max	°C / s
Time 25°C to Peak Temperature	$T_{to-peak}$	8 minutes max	min
Preheat			
Temperature min	T_{Smin}	150	°C
Temperature max	T_{Smax}	200	°C
Time T_{Smin} to T_{Smax}	t_s	60 – 180	sec
Soldering above liquidus			
Temperature liquidus	T_L	217	°C
Time above liquidus	t_L	60 – 150	sec
Peak temperature			
Peak Temperature	T_p	260	°C
Time within 5°C of peak temperature	t_p	20 – 40	sec

6.4. HANDLING PRECAUTIONS FOR MODULES WITH EMBEDDED CRYSTALS

The built-in AT-cut crystal consists of pure Silicon Dioxide in crystalline form. The cavity inside the package is evacuated and hermetically sealed in order for the crystal blank to function undisturbed from air molecules, humidity and other influences.

Shock and vibration:

Keep the crystal / module from being exposed to **excessive mechanical shock and vibration**. Micro Crystal guarantees that the crystal / module will bear a mechanical shock of 10000 g / 0.3 ms.

The following special situations may generate either shock or vibration:

Multiple PCB panels - Usually at the end of the pick & place process the single PCBs are cut out with a router. These machines sometimes generate vibrations on the PCB that have a fundamental or harmonic frequency close to the resonance frequency of the crystal unit. This might cause breakage of crystal blanks due to resonance. Router speed should be adjusted to avoid resonant vibration.

Ultrasonic cleaning - Avoid cleaning processes using ultrasonic energy. These processes can damage the crystals due to the mechanical resonance frequencies of the crystal blank.

Overheating, rework high temperature exposure:

Avoid overheating the package. The package is sealed with a seal ring consisting of 80% Gold and 20% Tin. The eutectic melting temperature of this alloy is at 280°C. Heating the seal ring up to >280°C will cause melting of the metal seal which then, due to the vacuum, is sucked into the cavity forming an air duct. This happens when using hot-air-gun set at temperatures >280°C.

Use the following methods for rework:

- Use a hot-air-gun set at 270°C.
- Use 2 temperature controlled soldering irons, set at 270°C, with special-tips to contact all solder-joints from both sides of the package at the same time, remove part with tweezers when pad solder is liquid.

7. COMPLIANCE INFORMATION

Micro Crystal confirms that the standard product Clock Oscillator MCSO2E is compliant with “EU RoHS Directive” and “EU REACH Directives”.

Please find the actual Certificate of Conformance for Environmental Regulations on our website:

[CoC Environment MCSO-Series.pdf](#)

8. DOCUMENT REVISION HISTORY

Date	Revision #	Revision Details
September 2016	2.0	Initial version
August 2021	3.0	New extended version

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